

IRL3202SPbF

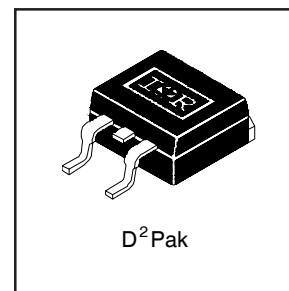
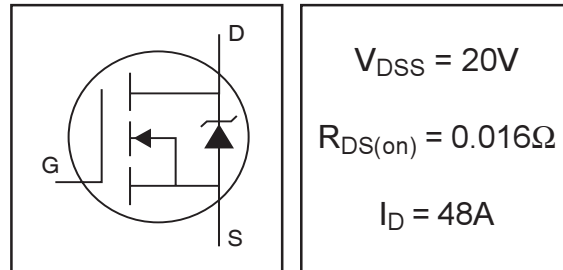
HEXFET® Power MOSFET

- Advanced Process Technology
- Surface Mount
- Optimized for 4.5V-7.0V Gate Drive
- Ideal for CPU Core DC-DC Converters
- Fast Switching
- Lead-Free

Description

These HEXFET Power MOSFETs were designed specifically to meet the demands of CPU core DC-DC converters in the PC environment. Advanced processing techniques combined with an optimized gate oxide design results in a die sized specifically to offer maximum efficiency at minimum cost.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5\text{V}$ Ⓞ	48	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5\text{V}$ Ⓞ	30	
I_{DM}	Pulsed Drain Current ① Ⓞ	190	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	69	W
	Linear Derating Factor	0.56	W/°C
V_{GS}	Gate-to-Source Voltage	± 10	V
V_{GSM}	Gate-to-Source Voltage (Start Up Transient, $t_p = 100\mu\text{s}$)	14	V
E_{AS}	Single Pulse Avalanche EnergyⓄ Ⓞ	270	mJ
I_{AR}	Avalanche CurrentⓄ	29	A
E_{AR}	Repetitive Avalanche EnergyⓄ	6.9	mJ
dv/dt	Peak Diode Recovery dv/dt Ⓞ Ⓞ	5.0	V/ns
T_J	Operating Junction and Storage Temperature Range	-55 to + 150	°C
T_{STG}			

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	1.8	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)**	---	40	

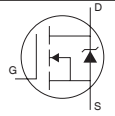
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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	20	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/°C	Reference to 25°C, I _D = 1mA ^①
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.019	Ω	V _{GS} = 4.5V, I _D = 29A ^④
		—	—	0.016		V _{GS} = 7.0V, I _D = 29A ^④
V _{GS(th)}	Gate Threshold Voltage	0.70	—	—	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	28	—	—	S	V _{DS} = 16V, I _D = 29A ^⑤
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 20V, V _{GS} = 0V
		—	—	250		V _{DS} = 10V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 10V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -10V
Q _g	Total Gate Charge	—	—	43	nC	I _D = 29A
Q _{gs}	Gate-to-Source Charge	—	—	12		V _{DS} = 16V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	13		V _{GS} = 4.5V, See Fig. 6 ^{④⑤}
t _{d(on)}	Turn-On Delay Time	—	9.8	—	ns	V _{DD} = 10V
t _r	Rise Time	—	100	—		I _D = 29A
t _{d(off)}	Turn-Off Delay Time	—	63	—		R _G = 9.5Ω, V _{GS} = 4.5V
t _f	Fall Time	—	82	—		R _D = 0.3Ω, ^{④⑤}
L _S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C _{iss}	Input Capacitance	—	2000	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	800	—		V _{DS} = 15V
C _{rss}	Reverse Transfer Capacitance	—	290	—		f = 1.0MHz, See Fig. 5 ^⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	48	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ^{①⑤}	—	—	190		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 29A, V _{GS} = 0V ^④
t _{rr}	Reverse Recovery Time	—	68	100	ns	T _J = 25°C, I _F = 29A
Q _{rr}	Reverse Recovery Charge	—	130	190	nC	di/dt = 100A/μs ^{④⑤}
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting T_J = 25°C, L = 0.64mH
R_G = 25Ω, I_{AS} = 29A.
- ③ I_{SD} ≤ 29A, di/dt ≤ 63A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Uses IRL3202 data and test conditions

** When mounted on FR-4 board using minimum recommended footprint.
For recommended footprint and soldering techniques refer to application note #AN-994.

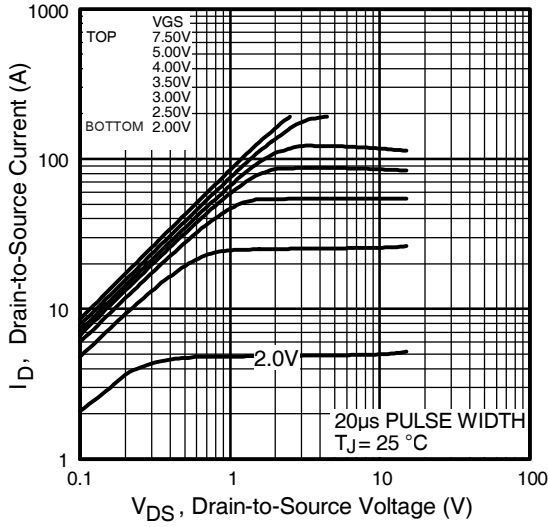


Fig 1. Typical Output Characteristics

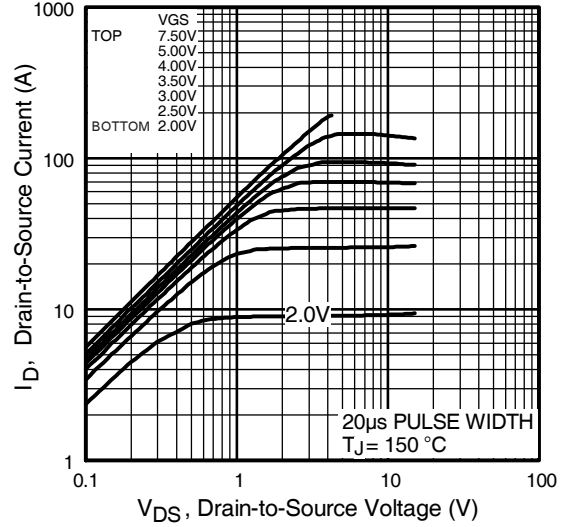


Fig 2. Typical Output Characteristics

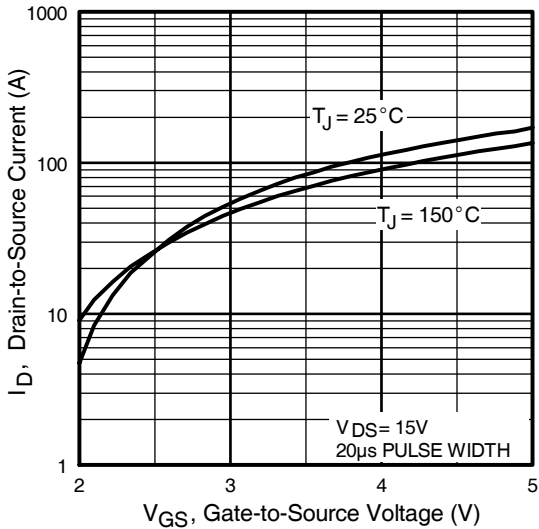


Fig 3. Typical Transfer Characteristics

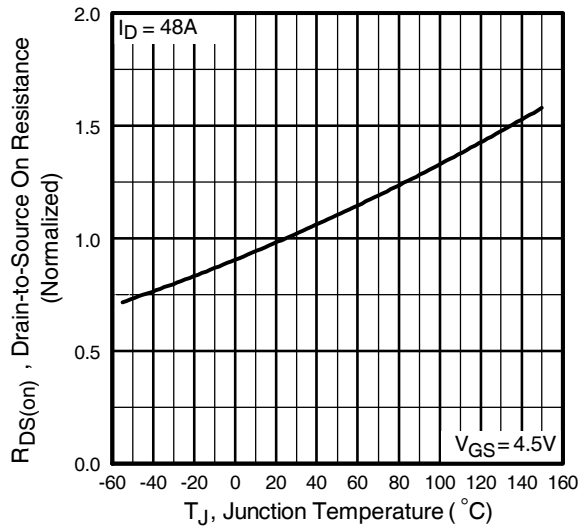


Fig 4. Normalized On-Resistance Vs. Temperature

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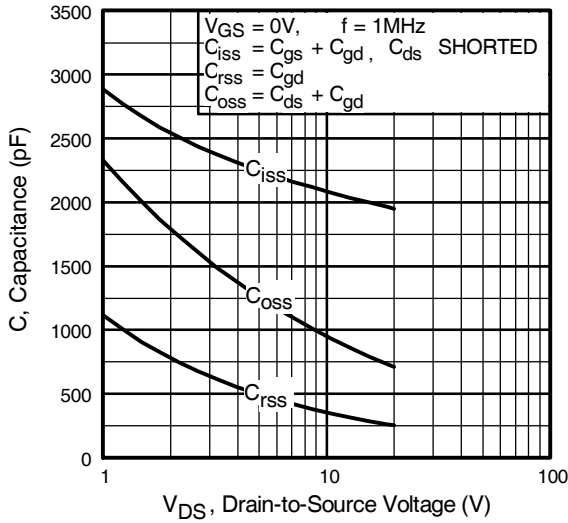


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

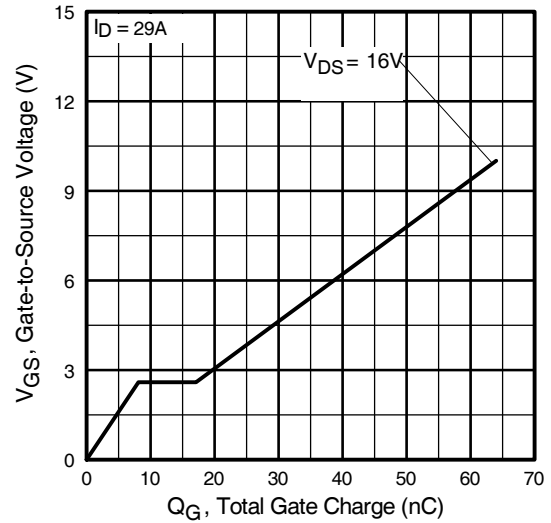


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

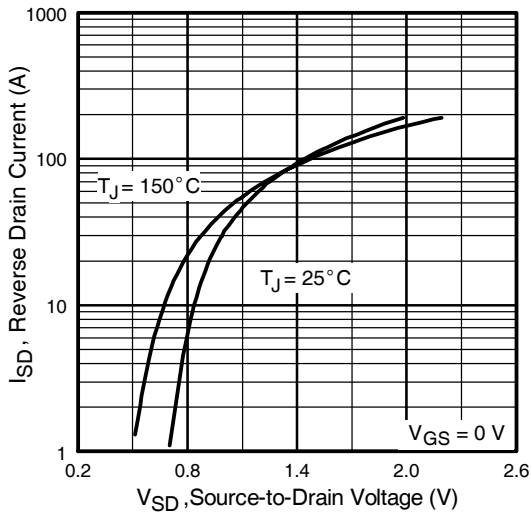


Fig 7. Typical Source-Drain Diode Forward Voltage

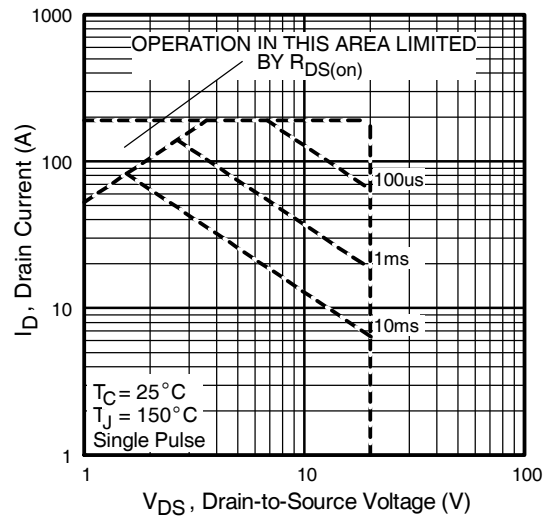


Fig 8. Maximum Safe Operating Area

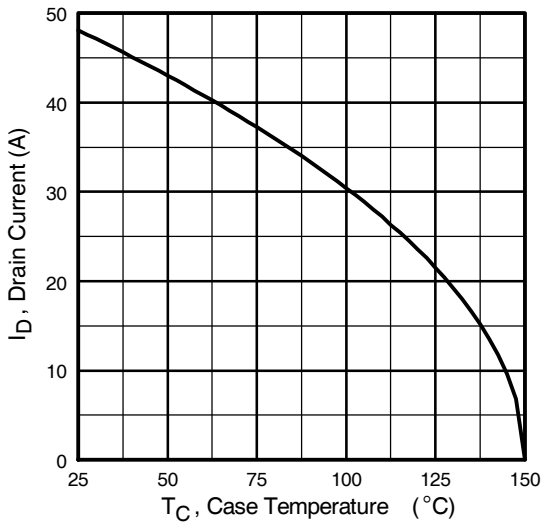


Fig 9. Maximum Drain Current Vs. Case Temperature

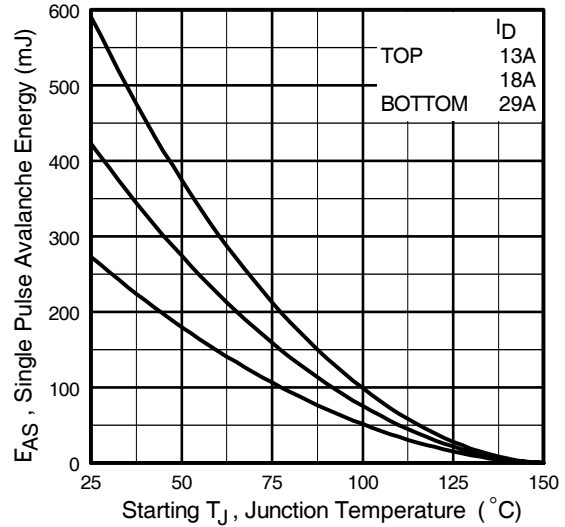


Fig 10. Maximum Avalanche Energy Vs. Drain Current

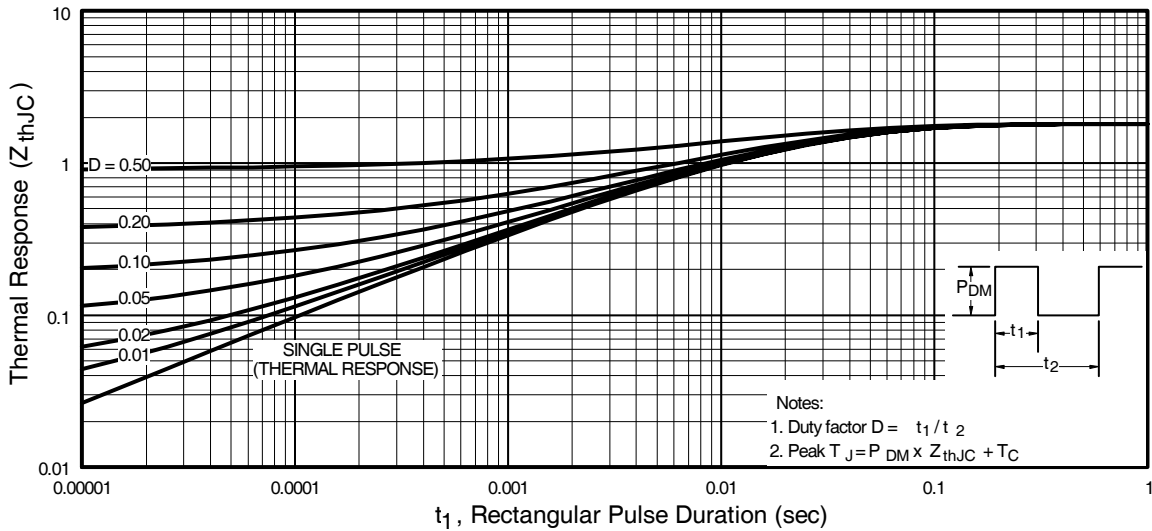


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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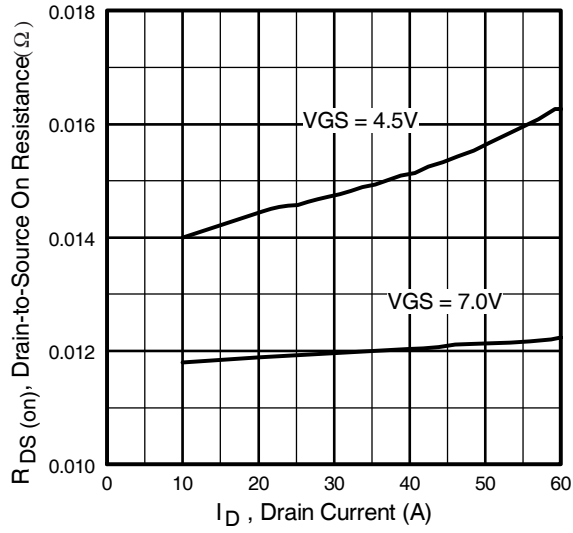


Fig 12. On-Resistance Vs. Drain Current

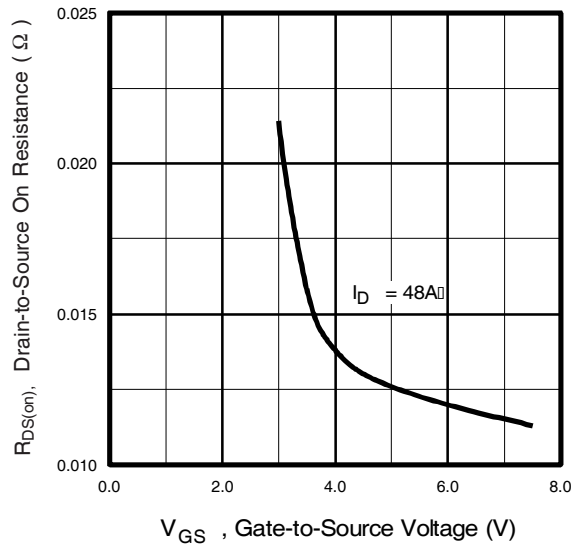
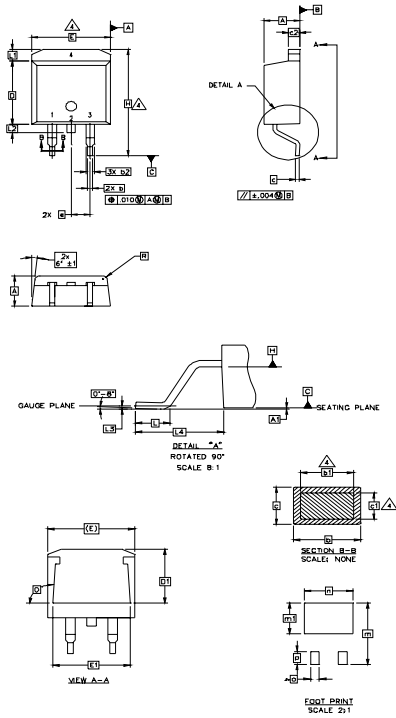


Fig 13. On-Resistance Vs. Gate Voltage

D²Pak Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 5. CONTROLLING DIMENSION: INCH.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.78	.045	.070	
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	4
c2	1.14	1.65	.045	.065	
D	8.51	9.65	.335	.380	3
D1	6.86		.270		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54	BSC	.100	BSC	
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	1.27	1.65	.050	.065	
L2	1.27	1.78	.050	.070	
L3	0.25	BSC	.010	BSC	
L4	4.78	5.28	.188	.208	
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
R	0.51	0.71	.020	.028	
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER

DIODES

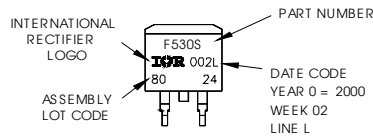
- 1.- ANODE *
- 2, 4.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

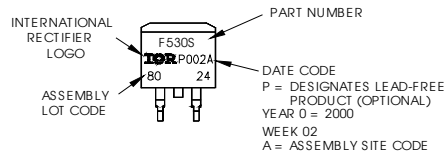
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"



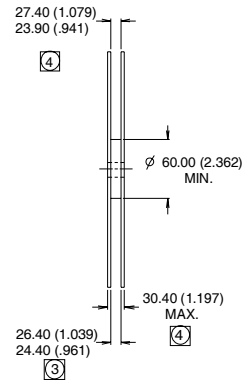
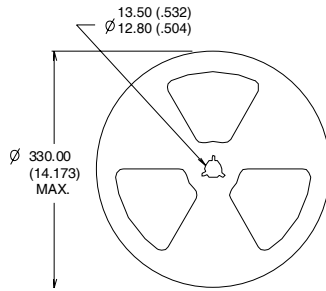
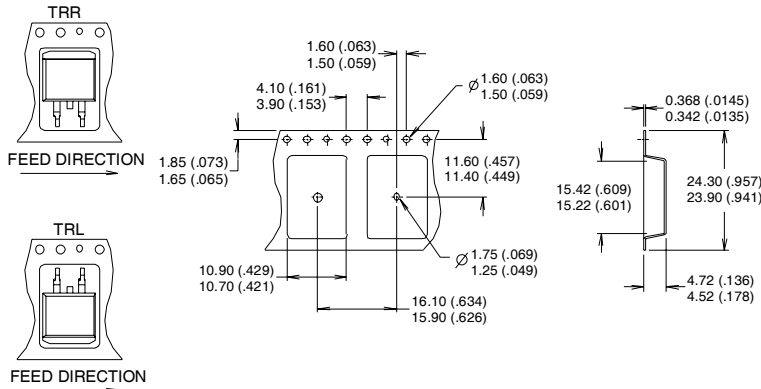
OR



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D²Pak Tape & Reel Information



- NOTES :
1. COMFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION MEASURED @ HUB.
 4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.

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Visit us at www.irf.com for sales contact information.12/04

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>